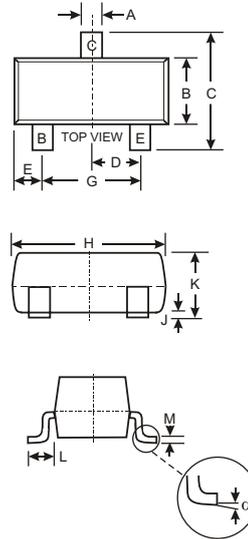


### Features

- Epitaxial Planar Die Construction.
- PNP complement:MMBT2907A
- Ideal for Medium Power Amplification and Switching.
- Marking Code:1P



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
$\alpha$	0°	8°
All Dimensions in mm		

### Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Collector-Base Voltage	V <sub>CB0</sub>	75	V
Emitter-Base Voltage	V <sub>EB0</sub>	6	V
Collector Current	I <sub>C</sub>	600	mA

### • THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,(1) TA=25°C Derate above 25°C	PD	225 1.8	mW mW/°C
Thermal Resistance,Junction to Ambient	R <sub>θJA</sub>	556	°C/W
Total Device Dissipation Alumina Substrate,(2) TA=25°C Derate above 25°C	PD	300 2.4	mW mW/°C
Thermal Resistance,Junction to Ambient	R <sub>θJA</sub>	417	°C/W
Junction and Storage Temperature	T <sub>j</sub> , T <sub>stg</sub>	-55 to +150	°C

1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

**Electrical Characteristics** @  $T_A = 25^\circ\text{C}$  unless otherwise specified

## OFF CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector–Emitter Breakdown Voltage ( $I_C = 10\text{ mA}$ , $I_B = 0$ )	VBR(CEO)	40	-	-	V
Collector–Base Breakdown Voltage ( $I_C = 10\text{ }\mu\text{A}$ , $I_E = 0$ )	VBR(CBO)	75	-	-	V
Emitter–Base Breakdown Voltage ( $I_E = 10\text{ }\mu\text{A}$ , $I_C = 0$ )	VBR(EBO)	6	-	-	V
Collector Cutoff Current ( $V_{CE} = 60\text{ V}$ , $V_{EB}(\text{off}) = 3.0\text{ V}$ )	ICEX	-	-	10	nA
Collector Cutoff Current ( $V_{CB} = 60\text{ V}$ , $I_E = 0$ ) ( $V_{CB} = 60\text{ V}$ , $I_E = 0$ , $T_A = 125^\circ\text{C}$ )	ICBO	-	-	0.01 10	$\mu\text{A}$
Emitter Cutoff Current ( $V_{EB} = 3.0\text{ V}$ , $I_C = 0$ )	IEBO	-	-	100	nA
Base Cutoff Current ( $V_{CE} = 60\text{ V}$ , $V_{EB}(\text{off}) = 3.0\text{ V}$ )	IBL	-	-	20	nA

## ON CHARACTERISTICS (Note 2.)

DC Current Gain ( $I_C = 0.1\text{ mA}$ , $V_{CE} = 10\text{ V}$ ) ( $I_C = 1.0\text{ mA}$ , $V_{CE} = 10\text{ V}$ ) ( $I_C = 10\text{ mA}$ , $V_{CE} = 10\text{ V}$ ) ( $I_C = 10\text{ mA}$ , $V_{CE} = 10\text{ V}$ , $T_A = -55^\circ\text{C}$ ) ( $I_C = 150\text{ mA}$ , $V_{CE} = 10\text{ V}$ ) ( $I_C = 150\text{ mA}$ , $V_{CE} = 1.0\text{ V}$ ) ( $I_C = 500\text{ mA}$ , $V_{CE} = 10\text{ V}$ )	HFE	35 50 75 35 100 50 40	- - - - - - -	- - - - 300 - -	
Collector–Emitter Saturation Voltage ( $I_C = 150\text{ mA}$ , $I_B = 15\text{ mA}$ ) ( $I_C = 500\text{ mA}$ , $I_B = 50\text{ mA}$ )	VCE(sat)	- -	- -	0.3 1	V
Base–Emitter Saturation Voltage ( $I_C = 150\text{ mA}$ , $I_B = 15\text{ mA}$ ) ( $I_C = 500\text{ mA}$ , $I_B = 50\text{ mA}$ )	VBE(sat)	0.6 -	- -	1.2 2	V

## SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ( $I_C = 20\text{ mA}$ , $V_{CE} = 20\text{ V}$ , $f = 100\text{ MHz}$ )	fT	300	-	-	MHz
Output Capacitance ( $V_{CB} = 5.0\text{ V}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	Cobo	-	-	8	pF
Input Capacitance ( $V_{EB} = 0.5\text{ V}$ , $I_C = 0$ , $f = 1.0\text{ MHz}$ )	Cibo	-	-	25	pF

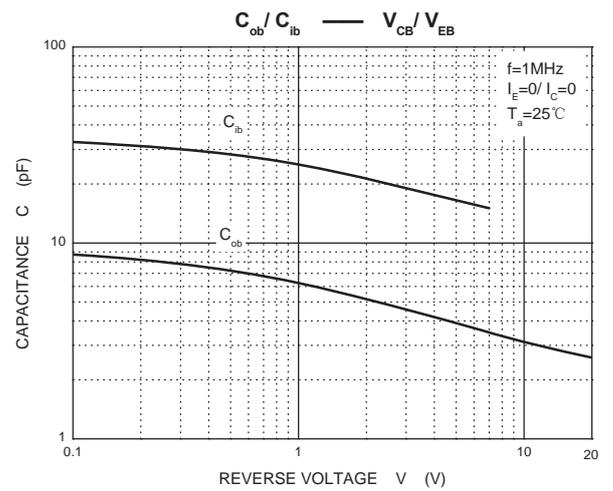
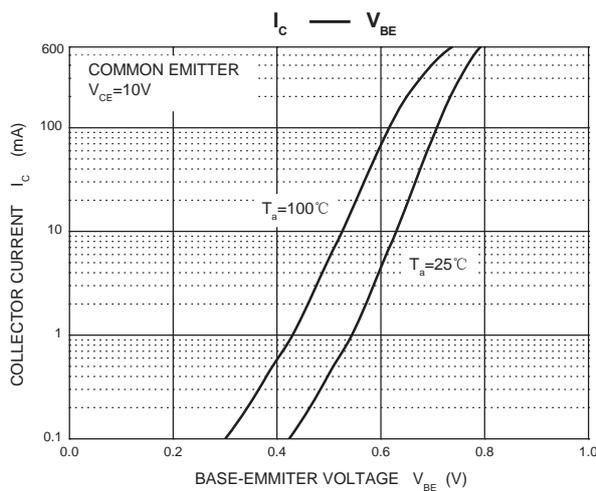
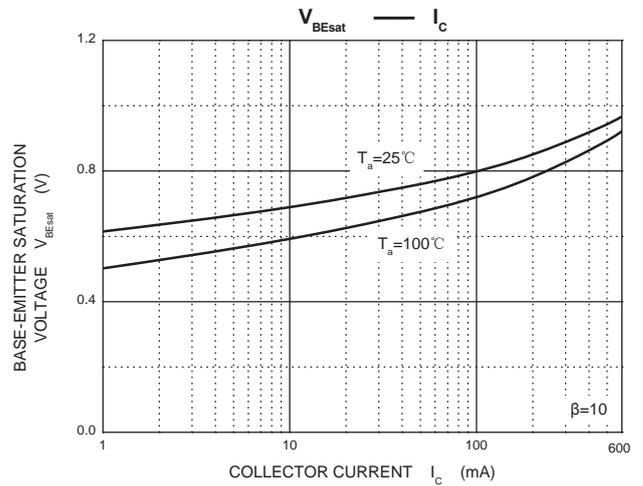
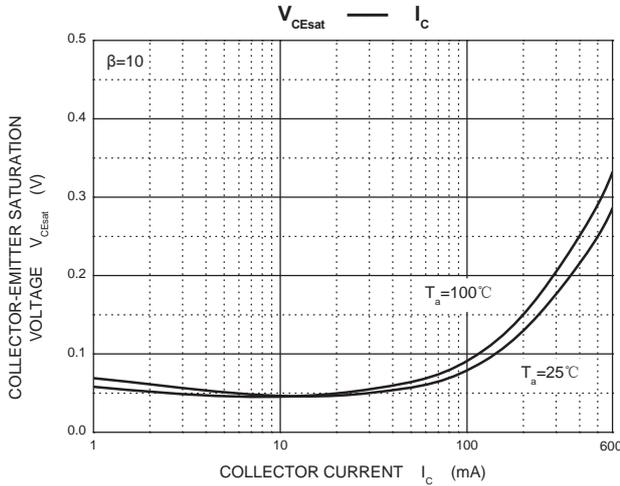
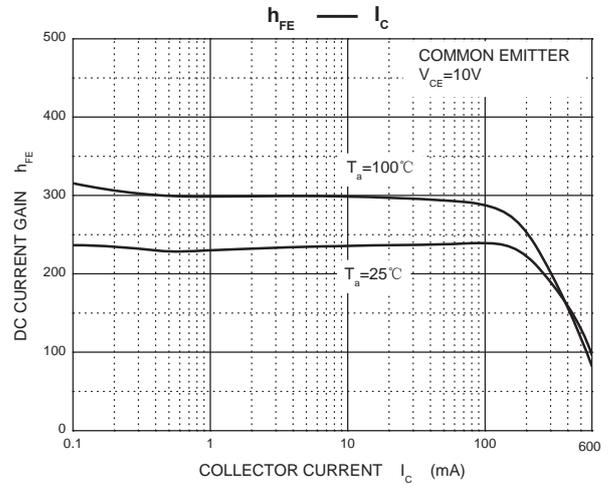
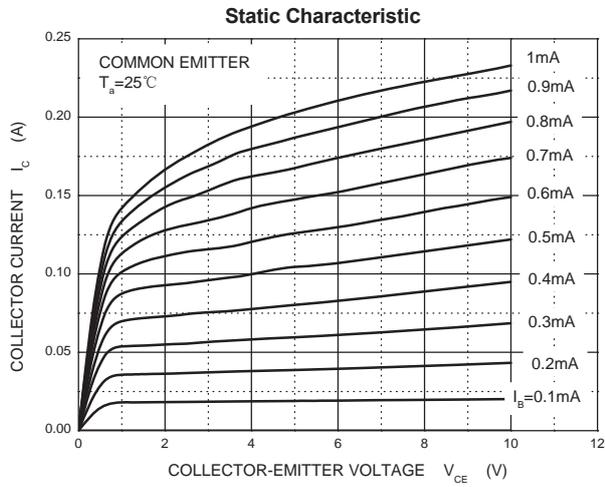
## SWITCHING CHARACTERISTICS

Delay Time	(VCC = 30 V, VEB = -0.5 V, IC = 150 mA, IB1 = 15 mA)	td	-	-	10	ns
Rise Time		tr	-	-	25	
Storage Time	(VCC = 30 V, IC = 150 mA, IB1 = IB2 = 15 mA)	ts	-	-	225	
Fall Time		tf	-	-	60	

2. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .



### TYPICAL TRANSIENT CHARACTERISTICS



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## **IMPORTANT NOTICE**

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